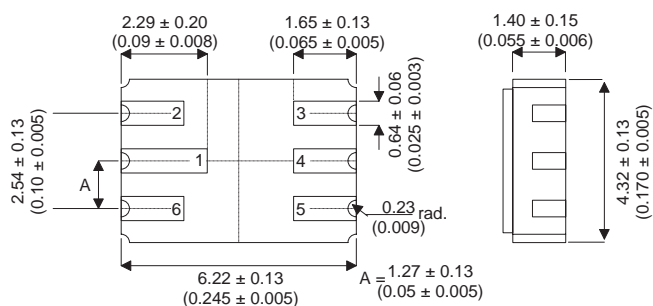


**SMALL SIGNAL DUAL
N-CHANNEL J-FET IN A
HERMETICALLY SEALED
CERAMIC SURFACE MOUNT PACKAGE
FOR HIGH RELIABILITY APPLICATIONS**

MECHANICAL DATA

Dimensions in mm (inches)



FEATURES

- HERMETIC CERAMIC SURFACE MOUNT PACKAGE
- CECC SCREENING OPTIONS
- SPACE QUALITY LEVELS OPTIONS

**LCC2 Package
Underside View**

- Pad 1 - Gate 1
- Pad 2 - Source 1
- Pad 3 - Drain 1
- Pad 4 - Gate 2
- Pad 5 - Source 2
- Pad 6 - Drain 2

APPLICATIONS:

Hermetically sealed dual surface mount version of the popular 2N4393 for high reliability / space applications requiring small size and low weight devices.

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^{\circ}C$ unless otherwise stated)		EACH SIDE	TOTAL DEVICE
V_{GD}	Gate – Drain Voltage	-35V	-35V
V_{GS}	Gate – Source Voltage	-35V	-35V
I_G	Gate Current	50mA	50mA
P_D	Power Dissipation	350mW	600mW/°C
	Derate	2.8mW/ °C	3.4mW/°C
T_j	Operating Junction Temperature Range	-55 to 150°C	-55 to 150°C
T_{stg}	Storage Temperature Range	-55 to 150°C	-55 to 150°C

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ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit		
STATIC CHARACTERISTICS							
$V_{(BR)GSS}$	Gate – Source Breakdown Voltage	$V_{DS} = 0V$	$I_G = -1\mu A$	-35	-55		V
$V_{GSS(off)}$	Gate – Source Cut-off Voltage	$V_{DS} = 15V$	$I_D = 10nA$	-0.5		-3	
I_{DSS}^*	Saturation Current	$V_{DS} = 20V$	$V_{GS} = 0V$	5			mA
I_{GSS}	Gate Reverse Current	$V_{GS} = -5V$			-5	-100	pA
		$V_{DS} = 0V$	$T_{amb} = 125^{\circ}\text{C}$		-3	-200	nA
$I_{D(off)}$	Drain Cut-off Current	$V_{DG} = 10V$	$V_{GS} = -10V$		5	100	pA
		$V_{DS} = 10V$	$V_{GS} = -10V$	$T_{amb} = 125^{\circ}\text{C}$	3	200	nA
$V_{DS(on)}$	Drain – Source On Voltage	$V_{GS} = 0V$	$I_D = 3mA$		0.25	0.4	V
$R_{DS(on)}$	Drain – Source On Resistance	$V_{GS} = 0V$	$I_D = 1mA$			100	Ω
DYNAMIC CHARACTERISTICS							
$R_{DS(on)}$	Drain – Source On Resistance	$V_{GS} = 0V$	$I_D = 0mA$			100	Ω
		$f = 1kHz$					
C_{ISS}	Common – Source Input Capacitance	$V_{DS} = 20V$	$V_{GS} = 0V$		13	16	pF
		$f = 1MHz$					
C_{RSS}	Common – Source Reverse Transfer Capacitance	$V_{DS} = 0V$	$V_{GS} = -5V$		4	5	pF
		$f = 1MHz$					
\bar{e}_n	Equivalent Input Noise Voltage	$V_{DG} = 10V$	$I_D = 10mA$		3.0		$\frac{nV}{\sqrt{Hz}}$
		$f = 1kHz$					

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